

In the Claims:

Please amend the claims as follows:

Claims 1-14 (canceled)

1 15. (Original) A method of making a MEMS apparatus, comprising:
2 a) providing a device component comprising single-crystal silicon;
3 b) creating at least one hinge in said device component;
4 c) constructing a support component having a cavity;
5 d) bonding said device component to said support component, such that said at
6 least one hinge is disposed within said cavity; and
7 e) forming in said device component a bulk element having a device surface
8 and a bottom surface, whereby said at least one hinge is coupled to said bulk
9 element and is disposed below said bottom surface, thereby suspending said
10 bulk element from said support.

1 16. (Original) The method of claim 15 wherein said device component comprises an
2 SOI (Silicon-On-Insulator) wafer having a single-crystal silicon device layer and a silicon
3 handle wafer sandwiching an insulation layer, said single-crystal silicon layer having a
4 first surface.

1 17. (Original) The method of claim 16 wherein said at least one hinge comprises first
2 and second hinge elements, fabricated on said first surface of said single-crystal silicon
3 device layer by a surface micromachining technique.

1 18. (Original) The method of claim 16 wherein said at least one hinge is created in said
2 single-crystal silicon device layer by a bulk micromachining technique.

1 19. (Original) The method of claim 17 wherein said step d) further includes removing
2 said silicon handle wafer along with said insulation layer, thereby revealing a second
3 surface of said single-crystal silicon device layer.

1 20. (Original) The method of claim 19 wherein said step e) includes using a bulk
2 micromachining technique to form said bulk element in said single-crystal silicon device

3 layer, whereby said first and second surfaces of said single-crystal silicon device layer
4 constitute said bottom and device surfaces of said bulk element.

1 21. (Original) The method of claim 15 further comprising the step of making said device
2 surface optically reflective.

1 22. (Original) The method of claim 21 wherein said device surface is made optically
2 reflective by depositing a reflective layer thereon.

1 23. (Original) The method of claim 15 wherein said device component comprises an
2 epitaxial silicon wafer.

1 24. (Original) The method of claim 15 wherein said support component is fabricated
2 out of an SOI wafer.

1 25. (Original) The method of claim 15 wherein said step c) further includes disposing at
2 least one electrode in said cavity.

Claims 26-32 (canceled)